

Bf998 datasheet pdf

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NotesDevice mounted on a N-Channel Dual Gate MOS-Fieldeffect Tetrode, Depletion Mode, BF Datasheet, BF circuit, BF data sheet: VISHAY, alldatasheet, Datasheet, Datasheet search site The transistors are protected against excessive input voltage surges by integrated back-to-back diodes between gates and source. NotesDevice mounted on a ceramic substrate,mm ×mm × mmDevice mounted on a printed-circuit board. The device is supplied in an antistatic package Silicon N-channel dual-gate MOS-FETs BF; BFR LIMITING VALUES In accordance with the Absolute Maximum Rating System (IEC). Depletion type field effect transistor in a plastic microminiature SOTB or SOTR package with source and substrate interconnected. Mechanical Data. Input and mixer stages in UHF tunersSOTR. Simplified outline (SOTB) and symbol; BF The device is supplied in an antistatic package. TS ≤°C, BF, BFR Ptot Storage temperature TStg°C Channel temperature Tch Thermal Resistance Parameter Symbol Value Unit Channel Applications. The gate-source input must be protected against static discharge during transport or handling DESCRIPTION. SYMBOL PARAMETER CONDITIONS MIN. MAX. UNIT VDS drain-source voltage –V ID drain current – Description. Typ: BF Case: SOT Plastic caseElectrostatic sensitive device Silicon N-channel dual-gate MOS-FETs, BF Datasheet, BF circuit, BF data sheet: PHILIPS, alldatasheet, Datasheet, Datasheet search site for Electronic Silicon N-channel dual-gate MOS-FETs BF; BFR LIMITING VALUES In accordance with the Absolute Maximum Rating System (IEC). The transistors are protected against excessive input voltage surges by integrated back-to-back diodes between gates and source Silicon N-channel dual-gate MOS-FETs, BF Datasheet, BF circuit, BF data sheet: PHILIPS, alldatasheet, Datasheet, Datasheet search site for Electronic Components and Semiconductors, integrated circuits, diodes, triacs and other semiconductors Depletion type field-effect transistor in a plastic microminiature SOTR package with source and substrate interconnected. The BF isV,mA, N-Channel MOSFET, Transistor. The transistor is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

 Difficulté **Moyen**

 Durée **749 minute(s)**

 Catégories **Vêtement & Accessoire, Décoration, Bien-être & Santé, Recyclage & Upcycling, Science & Biologie**

 Coût **320 USD (\$)**

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